Silicon PNP Power Transistors

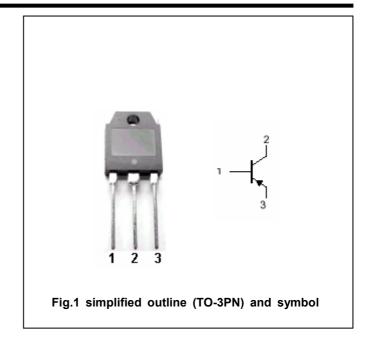
BD250/A/B/C

DESCRIPTION

- ·With TO-3PN package
- ·Complement to type BD249/A/B/C
- ·125 W at 25°C case temperature
- ·25 A continuous collector current

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	BD246		-55		
		BD246A	Collector emitter	-70		
		BD246B	Collector emitter	-90	V	
		BD246C		-115	1	
	Collector-emitter voltage	BD246		-45		
$V_{\sf CEO}$		BD246A	Open base	-60		
		BD246B		-80	V	
		BD246C		-100		
V _{EBO}	Emitter-base voltage		Open collector	-5	V	
I _C	Collector current			-25	Α	
I _{CM}	Collector current-peak			-40	Α	
I _B	Base current			-5	Α	
Pc	Collector power dissipation		T _C =25□	125	W	
T _j	Junction temperature			-65~150		
T _{stg}	Storage temperature			-65~150		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case		□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	BD250	– I _C =-30mA ;I _B =0	-45			V
		BD250A		-60			
		BD250B		-80			
		BD250C		-100			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =-15A ;I _B =-1.5A			-1.8	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =-25A ;I _B =-5A			-4.0	V
V_{BE-1}	Base-emitter on voltage		I _C =-15A ; V _{CE} =-4V			-1.6	V
V_{BE-2}	Base-emitter on voltage		I _C =-25A ; V _{CE} =-4V			-3.0	٧
I _{CEO}	Collector cut-off current	BD250/250A	V _{CE} =-30V I _B =0			-1.0	mA
		BD250B/250C	V _{CE} =-60V I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain		I _C =-1.5A ; V _{CE} =-4V	25			
h _{FE-2}	DC current gain		I _C =-15A ; V _{CE} =-4V	10			
h _{FE-3}	DC current gain		I _C =-25A ; V _{CE} =-4V	5			
Switching ti	mes						
t _{on}	Turn-on time	I _C =-5A; I _{B1} =-I _{B2} =-0.5A			0.2		μs
t _{off}	Turn-off time		R _L =5Ω		0.4		μs

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PACKAGE OUTLINE

